



High Performance InGaAs p-i-n Photodiode

'ST' Active Device Mount

13PD150-ST

The 13PD150-ST, an InGaAs photodiode with a 150 μ m-diameter photosensitive region packaged in a TO-46 header and aligned in an AT&T ST active device mount, is intended for high coupling efficiency to multi-mode fiber in moderate-to-high speed applications. Planar semiconductor design and dielectric passivation provide low noise performance. Reliability is assured by hermetic sealing and a 100% purge burn-in (200°C, 15 hours, $V_r = 20V$). The ST receptacle is suitable for bulkhead and PC board mounting.

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics:						
Parameters	Test Conditions	Min	Typ	Max	Units	
Operating Voltage	-	-	-	-20	Volts	
Dark Current	-5V	-	0.5	2.5	nA	
Capacitance	-5V	-	1.5	2.25	pF	
Responsivity	1300nm	0.7	0.8	-	A/W	
Rise/Fall	-	-	-	0.5	ns	
Absolute Maximum Ratings						
Reverse Voltage						20 Volts
Forward Current						5 mA
Reverse Current						1 mA
Operating Temperature						-40°C to + 85°C
Storage Temperature						-40°C to + 85°C
Soldering Temperature						250°C